TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD1008SA

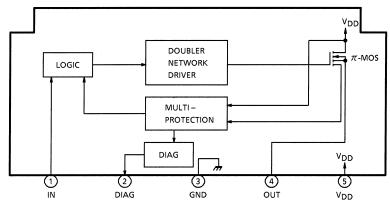
High-side Power Switch for Motors, Solenoids, and Lamp Drivers

The TPD1008SA is a monolithic power IC for high-side switches. The IC has a vertical MOS FET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). The device offers intelligent self-protection and diagnostic functions.

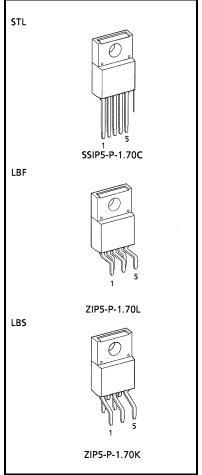
Features

- A monolithic power IC with a new structure combining a control block (Bi–CMOS) and a vertical power MOS FET (π –MOS) on a single chip
- One side of load can be grounded to a high-side switch.
- Can directly drive a power load from a microprocessor.
- Built-in protection against thermal shutdown and load short circuiting
- Incorporates a diagnosis function that allows diagnosis output to be read externally at load short-circuiting, opening, or overtemperature.
- Up to -10V of counter-electromotive force from an L load can be applied.
- Low on-resistance : $RDS(ON) = 200m\Omega(max)$
- Low operating current : IDD = 1mA (typ.) (@VDD = 12V, VIN = 0V)
- 5-pin TO-220 insulated package
- Three standard lead configurations

Pin Assignment



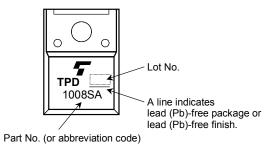
Note: Due to its MOS structure, this product is sensitive to static electricity.



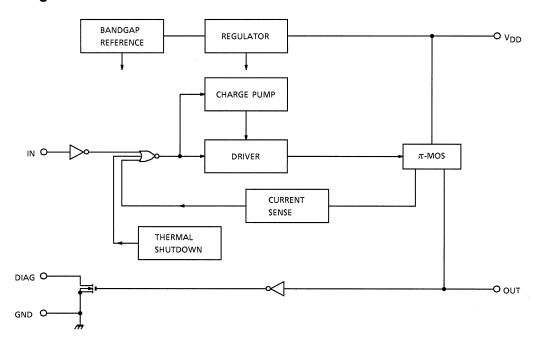
Weight

SSIP5-P-1.70C : 2.1g (typ.) ZIP5-P-1.70L : 2.1g (typ.) ZIP5-P-1.70K : 2.1g (typ.)

Marking



Block Diagram



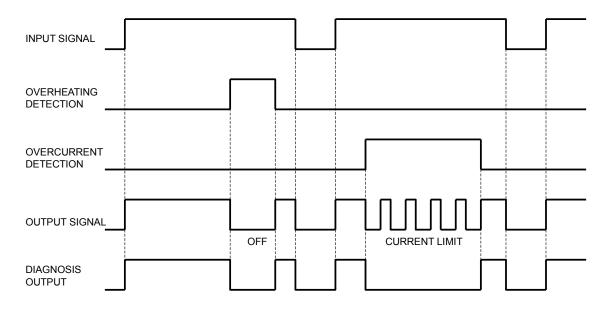
Pin Description

Pin No.	Symbol	Function
1	IN	Input is CMOS-compatible, with pull-down resistor connected. Even if the input is open, output will not accidentally turn on.
2	DIAG	Self-diagnosis detection pin. Goes low when overheating is detected or when output is short-circuited with input on (high). n-channel open drain.
3	GND	Ground pin.
4	OUT	When the load is short-circuited and current in excess of the detection current flows to the output pin, the output automatically turns on or off.
5	V_{DD}	Power pin.

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2004-07-01

Timing Chart



Truth Table

Input Signal	Output Signal	Diagnosis Output	State	
Н	Н	Н	Normal	
L	L	L	Nomia	
Н	L	L	Load short circuited	
L	L	L	Load Short Circuited	
Н	Н	Н	Load open	
L	Н	Н	Load open	
Н	L	L	Overtemperature	
L	L	L	Overtemperature	

Maximum Ratings (Ta = 25°C)

Characteris	tics	Symbol	Rating	Unit
Drain-source Voltage		V _{DS}	60	V
Supply Voltage	DC	V _{DD (1)}	DD (1) 25	
Supply Vollage	Pulse	V _{DD (2)}	60 (Rs = 1Ω, τ = 250ms)	V
Input Voltage	DC	V _{IN (1)}	-0.5~12	V
input voitage	Pulse	V _{IN (2)}	V _{DD (1)} + 1.5 (t = 100ms)	V
Diagnosis Output Volta	ge	V_{DIAG}	-0.5~25	٧
Output Current		Io	Internally Limited	Α
Input Current		I _{IN}	±10	mA
Diagnosis Output Curre	ent	I _{DIAG}	5	mA
Power Dissipation	Tc = 25°C	P _{D (1)}	30	W
Fower Dissipation	Ta = 25°C	P _{D (2)}	2	W
Operating Temperature	;	T _{opr}	-40~110	°C
Junction Temperature		Tj	150	°C
Storage Temperature		T _{stg}	-55~150	°C
Lead Temperature/Time	е	T _{SOL}	275 (5s), 260 (10s)	°C

Electrical Characteristics ($T_C = -40\sim110^{\circ}C$, $V_{DD} = 8\sim18V$)

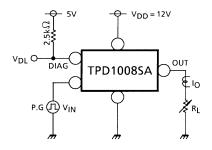
Characteri	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Operating Supply Volt	V _{DD (opr)}	_	_	5	12	18	V	
Supply Current	Supply Current		_	V _{DD} = 12V, V _{IN} = 0V	_	1	5	mA
Input Voltage		V _{IH}	_	V _{DD} = 12V, I _O = 2A	3.5	-	_	٧
		V _{IL}	_	V _{DD} = 12V, I _O = 1.2mA	_	_	1.5	V
Input Current		I _{IN (1)}		V _{DD} = 12V, V _{IN} = 5V	_	50	200	μΑ
		I _{IN (2)}		V _{DD} = 12V, V _{IN} = 0V	-0.2	_	0.2	μA
On Voltage		V _{DS (ON)}	_	V _{DD} = 12V, I _O = 2A, T _C = 25°C	_	_	0.4	V
On Resistance		R _{DS (ON)}	_	V _{DD} = 12V, I _O = 2A, T _C = 25°C	_	_	0.2	Ω
Output Leakage Current		I _{OL}	_	V _{DD} = 18V, V _{IN} = 0V	_	_	1.2	mA
Diagnosis Output Voltage	"L" Level	V _{DL}	_	V _{DD} = 12V, I _{DL} = 2mA	_	_	0.4	V
Diagnosis Output Current	"H" Level	I _{DH}	_	V _{DD} = 18V, V _{DH} = 18V	_	_	10	μA
Overcurrent Protection		I _{S (1)} (Note 1)	1	V - 40V T - 05°C	4	6	8	Α
		I _{S (2)} (Note 2)	2	V _{DD} = 12V, T _C = 25°C	4	8	12	Α
Thermal Shutdown	Temperature	T _S		_	150	160	200	°C
	Hysteresis	ΔT _S		_	_	10	_	°C
Open Detection Resis	pen Detection Resistance			V _{DD} = 8V	1	20	100	kΩ
Switching Time		t _{ON}	- 3	V _{DD} = 12V, R _L = 5Ω T _C = 25°C	10	100	_	μs
		t _{OFF}			10	30	_	μs

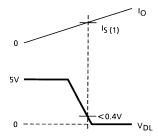
Note 1: Overcurrent detection value when load is short-circuited and VIN = "L" \rightarrow "H"

Note 2: Overcurrent detection value when load current is increased while V_{IN} = "H"

Test Circuit 1

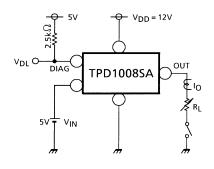
Overcurrent Detection

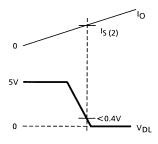




Test Circuit 2

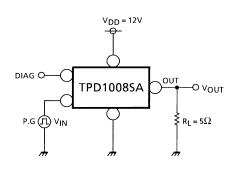
Overcurrent Detection

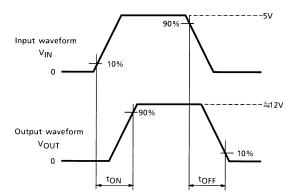


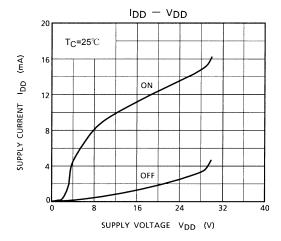


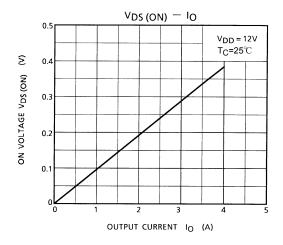
Test Circuit 3

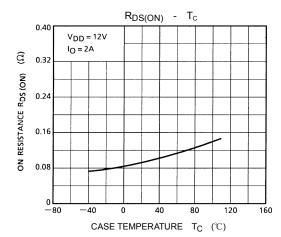
Switching Time

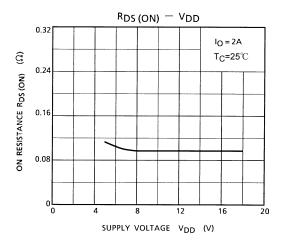


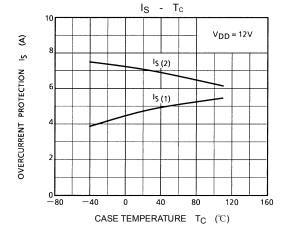


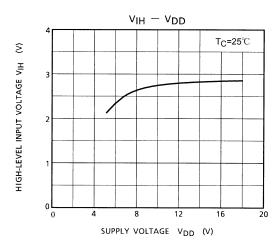


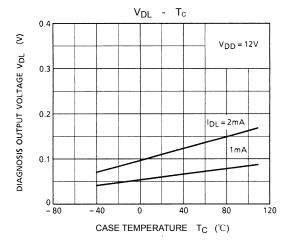


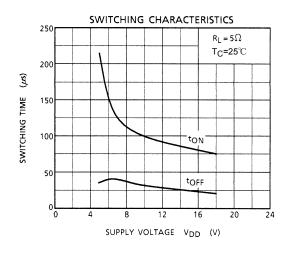


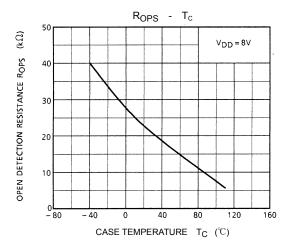


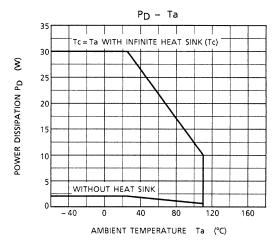


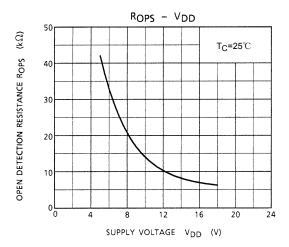








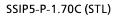


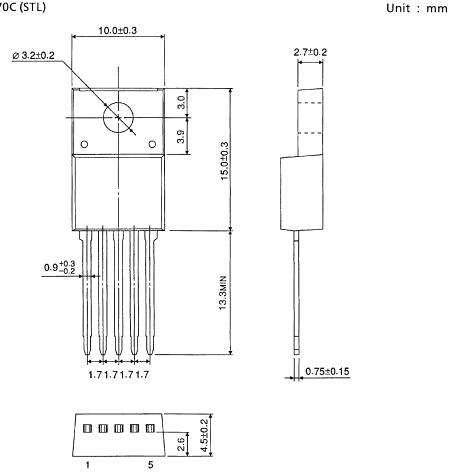


Precaution

1. Since there is no built-in protection against reverse connection of batteries, etc., provide such protection using external circuits.

Package Dimensions

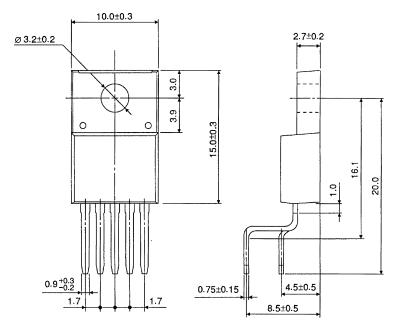


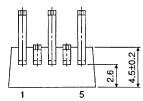


Weight: 2.1g (typ.)

Package Dimensions

ZIP5-P-1.70L (LBF) Unit: mm



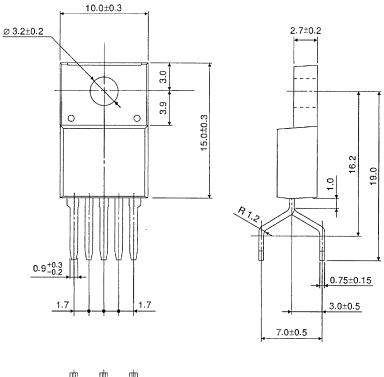


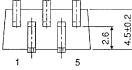
Weight: 2.1g (typ.)

Unit: mm

Package Dimensions

ZIP5-P-1.70K (LBS)





Weight: 2.1g (typ.)

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